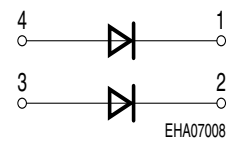
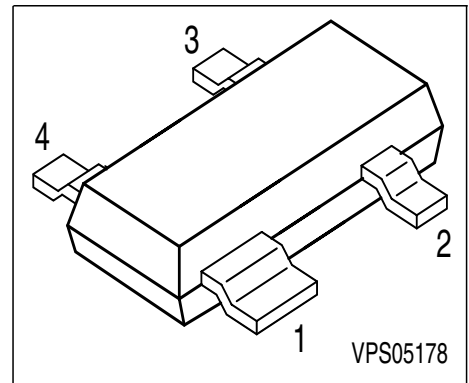


**Silicon Schottky Diodes**

- For mixer applications in the VHF / UHF range
- For high-speed switching applications



**ESD: Electrostatic discharge sensitive device, observe handling precaution!**

Type	Marking	Pin Configuration				Package
BAT 68-07	87s	1 = C1	2 = C2	3 = A2	4 = A1	SOT-143

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Diode reverse voltage	$V_R$	8	V
Forward current	$I_F$	130	mA
Total power dissipation, $T_S \leq 60\text{ °C}$	$P_{tot}$	150	mW
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 ... 150	

**Thermal Resistance**

Junction - ambient <sup>1)</sup>	$R_{thJA}$	$\leq 750$	K/W
Junction - soldering point	$R_{thJS}$	$\leq 590$	

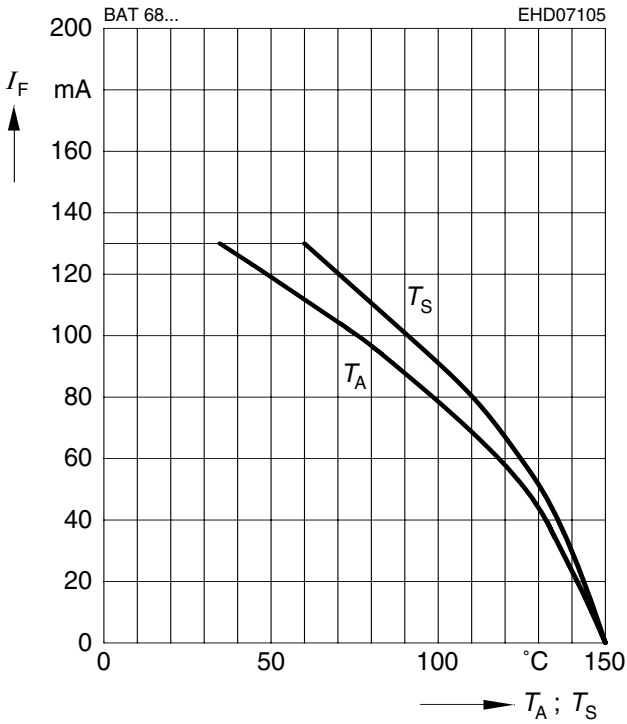
1) Package mounted on alumina 15mm x 17.6mm x 0.7mm)

**Electrical Characteristics** at  $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC characteristics</b>					
Breakdown voltage $I_{(BR)} = 10\text{ }\mu\text{A}$	$V_{(BR)}$	8	-	-	V
Reverse current $V_R = 1\text{ V}$	$I_R$	-	-	0.1	$\mu\text{A}$
Reverse current $V_R = 1\text{ V}, T_A = 60\text{ }^\circ\text{C}$	$I_R$	-	-	1.2	
Forward voltage $I_F = 1\text{ mA}$ $I_F = 10\text{ mA}$	$V_F$	-	-	340 500	mV
<b>AC characteristics</b>					
Diode capacitance $V_R = 0\text{ V}, f = 1\text{ MHz}$	$C_T$	-	-	1	pF
Differential forward resistance $I_F = 5\text{ mA}, f = 10\text{ kHz}$	$R_f$	-	-	10	$\Omega$

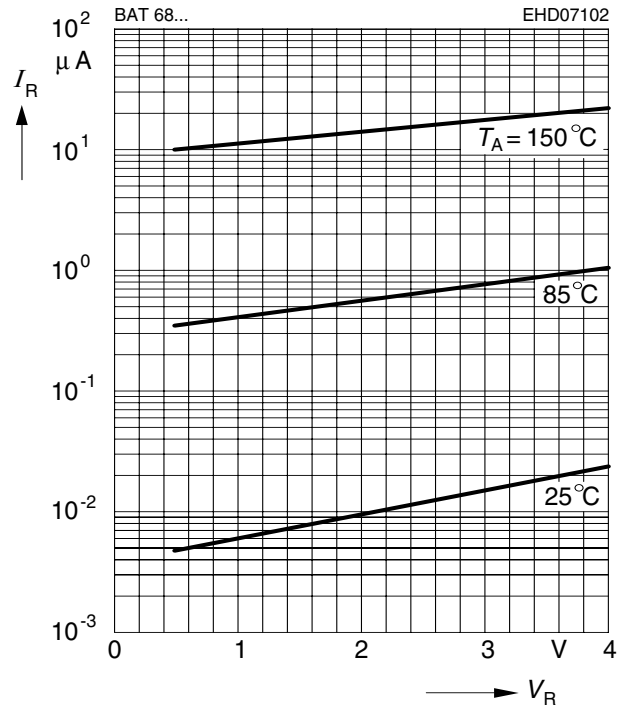
**Forward current  $I_F = f(T_A^*; T_S)$**

\* Package mounted on alumina



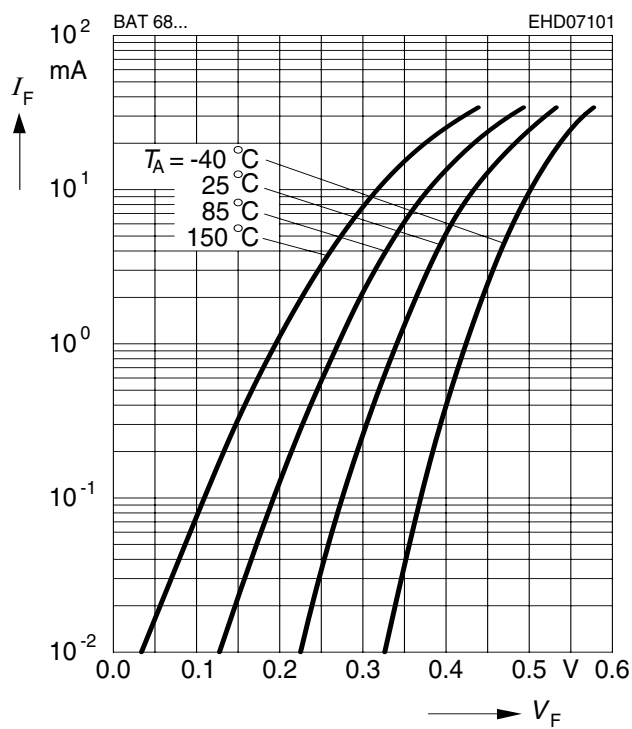
**Reverse current  $I_R = f(V_R)$**

$T_A =$  Parameter



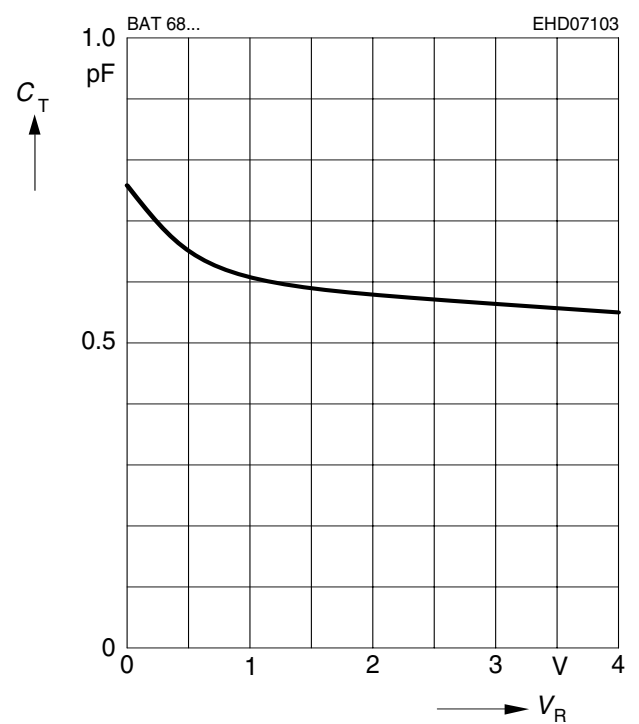
**Forward current  $I_F = f(V_F)$**

$T_A =$  Parameter



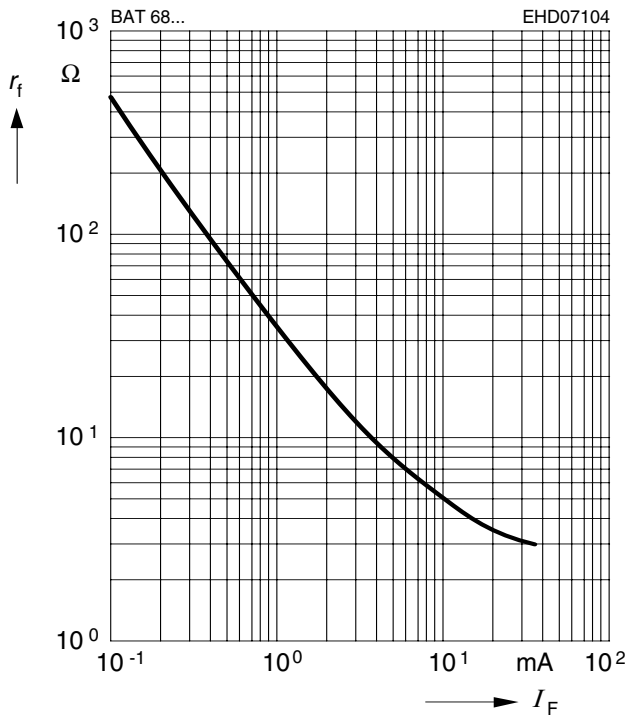
**Diode capacitance  $C_T = f(V_R)$**

$f = 1\text{MHz}$



Differential forward resistance  $r_f = f(I_F)$

$f = 10 \text{ kHz}$



This datasheet has been download from:

[www.datasheetcatalog.com](http://www.datasheetcatalog.com)

Datasheets for electronics components.